

Chipsmall Limited consists of a professional team with an average of over 10 year of expertise in the distribution of electronic components. Based in Hongkong, we have already established firm and mutual-benefit business relationships with customers from, Europe, America and south Asia, supplying obsolete and hard-to-find components to meet their specific needs.

With the principle of "Quality Parts, Customers Priority, Honest Operation, and Considerate Service", our business mainly focus on the distribution of electronic components. Line cards we deal with include Microchip, ALPS, ROHM, Xilinx, Pulse, ON, Everlight and Freescale. Main products comprise IC, Modules, Potentiometer, IC Socket, Relay, Connector. Our parts cover such applications as commercial, industrial, and automotives areas.

We are looking forward to setting up business relationship with you and hope to provide you with the best service and solution. Let us make a better world for our industry!



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General Purpose Transistors

PNP Silicon

Features

- S Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable
- These Devices are Pb–Free, Halogen Free/BFR Free and are RoHS Compliant

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector – Emitter Voltage	V_{CEO}	-45	V
Collector – Base Voltage	V_{CBO}	-50	V
Emitter – Base Voltage	V_{EBO}	-5.0	V
Collector Current – Continuous	I _C	-500	mAdc

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation FR-5 Board, (Note 1) T _A = 25°C Derate above 25°C	P _D	225 1.8	mW mW/°C
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	556	°C/W
Total Device Dissipation Alumina Substrate, (Note 2) T _A = 25°C Derate above 25°C	P _D	300 2.4	mW mW/°C
Thermal Resistance, Junction-to-Ambient	R _{θJA} 417		°C/W
Junction and Storage Temperature	T _J , T _{stg}	-55 to +150	°C

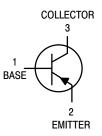
Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

- 1. $FR-5 = 1.0 \times 0.75 \times 0.062$ in.
- 2. Alumina = 0.4 x 0.3 x 0.024 in 99.5% alumina.



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SOT-23 CASE 318 STYLE 6

MARKING DIAGRAM



 $5xx = Device\ Code$ $xx = A1,\ B1,\ or\ C$

M = Date Code*

= Pb-Free Package

(Note: Microdot may be in either location)
*Date Code orientation and/or overbar may vary depending upon manufacturing location.

ORDERING INFORMATION

See detailed ordering and shipping information on page 2 of this data sheet.

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted.)

Characteristic	Symbol	Min	Тур	Max	Unit		
OFF CHARACTERISTICS							
Collector – Emitter Breakdown Voltage (I _C = -10 mA)		V _{(BR)CEO}	-45	-	_	V	
Collector – Emitter Breakdown Voltage $(V_{EB}=0, I_{C}=-10 \mu A)$		V _{(BR)CES}	-50	-	-	V	
Emitter – Base Breakdown Voltage ($I_E = -1.0 \mu A$)		V _{(BR)EBO}	-5.0	-	-	V	
Collector Cutoff Current $(V_{CB} = -20 \text{ V})$ $(V_{CB} = -20 \text{ V}, T_{J} = 150^{\circ}\text{C})$		Ісво	_ _	- -	-100 -5.0	nA μA	
ON CHARACTERISTICS							
DC Current Gain $(I_C = -100 \text{ mA}, V_{CE} = -1.0 \text{ V})$ $(I_C = -500 \text{ mA}, V_{CE} = -1.0 \text{ V})$	BC807–16, SBC80–16L BC807–25, SBC807–25L BC807–40, SBC807–40L	h _{FE}	100 160 250 40	- - -	250 400 600 –	-	
Collector – Emitter Saturation Voltage (I _C = -500 mA, I _B = -50 mA)		V _{CE(sat)}	-	-	-0.7	V	
Base – Emitter On Voltage (I _C = –500 mA, V _{CE} = –1.0 V)		V _{BE(on)}	-	-	-1.2	V	
SMALL-SIGNAL CHARACTERISTICS							
Current – Gain – Bandwidth Product (I _C = -10 mA, V _{CE} = -5.0 Vdc, f = 100 MHz)		f _T	100	-	_	MHz	
Output Capacitance (V _{CB} = -10 V, f = 1.0 MHz)		C _{obo}	-	10	_	pF	

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

ORDERING INFORMATION

Device	Specific Marking	Package	Shipping [†]		
BC807-16LT1G	544		0000 / Tara o Basil		
SBC807-16LT1G*	5A1		3000 / Tape & Reel		
BC807-16LT3G	544		40.000 / Tara 0 Basil		
SBC807-16LT3G*	5A1		10,000 / Tape & Reel		
BC807-25LT1G	ED4	504	0000 / Tara - 0 David		
SBC807-25LT1G*	5B1	SOT-23	3000 / Tape & Reel		
BC807-25LT3G	ED1	(Pb-Free) 5B1	10 000 / Tana 9 Daal		
SBC807-25LT3G*	361		10,000 / Tape & Reel		
BC807-40LT1G	5C		2000 / Tana & Dool		
SBC807-40LT1G*	50		3000 / Tape & Reel		
BC807-40LT3G	50		10.000 / Tone 9. Dool		
SBC807-40LT3G*	5C		10,000 / Tape & Reel		

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

^{*}S Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable.

TYPICAL CHARACTERISTICS - BC807-16LT1

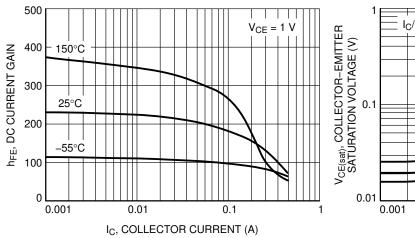


Figure 1. DC Current Gain vs. Collector Current

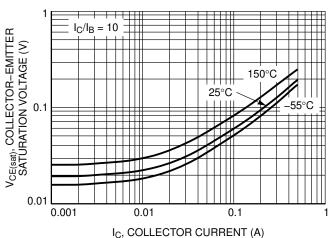


Figure 2. Collector Emitter Saturation Voltage vs. Collector Current

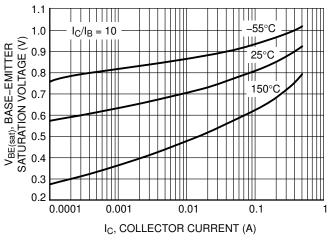


Figure 3. Base Emitter Saturation Voltage vs.
Collector Current

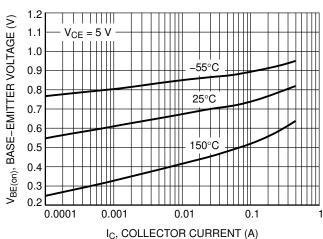


Figure 4. Base Emitter Voltage vs. Collector Current

TYPICAL CHARACTERISTICS - BC807-16LT1

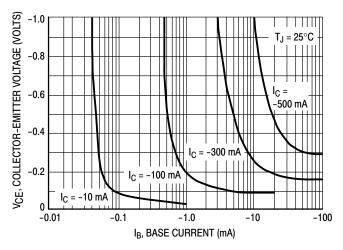


Figure 5. Saturation Region

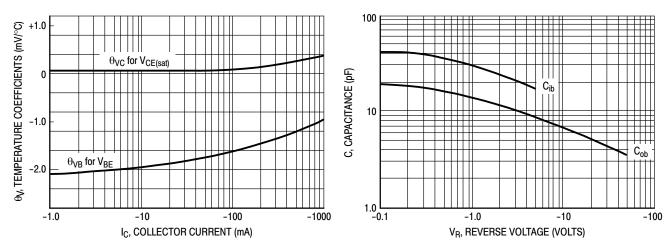


Figure 6. Temperature Coefficients

Figure 7. Capacitances

TYPICAL CHARACTERISTICS - BC807-25LT1

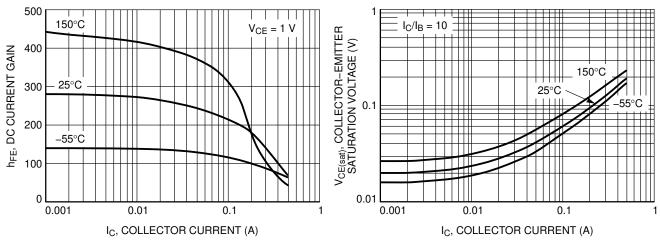


Figure 8. DC Current Gain vs. Collector Current

Figure 9. Collector Emitter Saturation Voltage vs. Collector Current

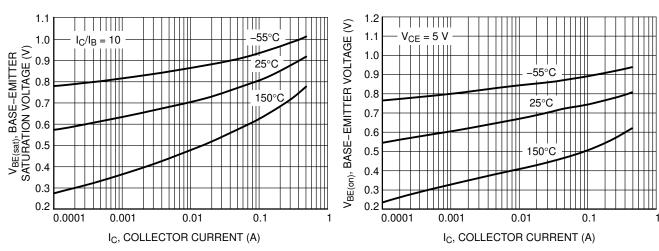


Figure 10. Base Emitter Saturation Voltage vs.
Collector Current

Figure 11. Base Emitter Voltage vs. Collector Current

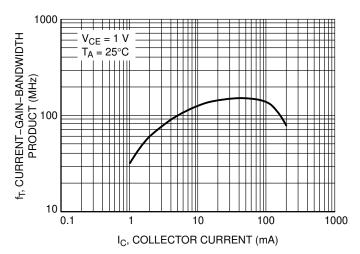


Figure 12. Current Gain Bandwidth Product vs. Collector Current

TYPICAL CHARACTERISTICS - BC807-25LT1

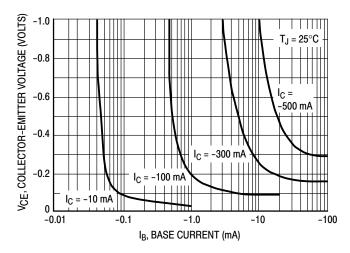


Figure 13. Saturation Region

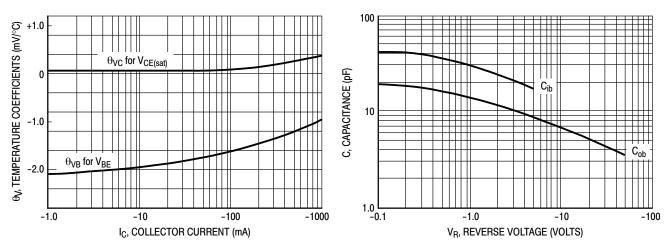


Figure 14. Temperature Coefficients

Figure 15. Capacitances

TYPICAL CHARACTERISTICS - BC807-40LT1

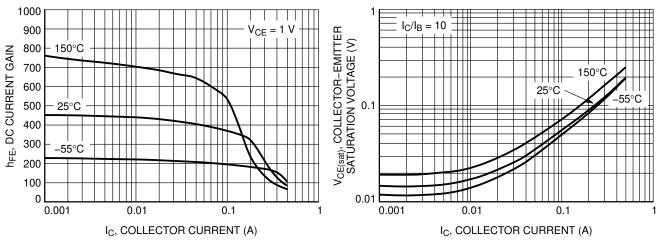


Figure 16. DC Current Gain vs. Collector Current

Figure 17. Collector Emitter Saturation Voltage vs. Collector Current

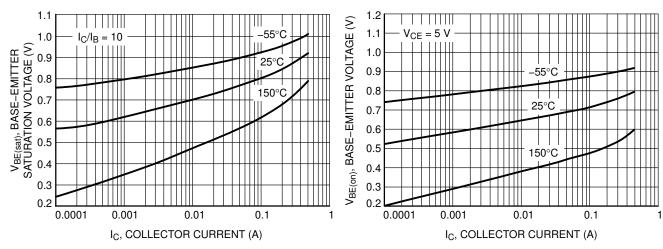


Figure 18. Base Emitter Saturation Voltage vs.
Collector Current

Figure 19. Base Emitter Voltage vs. Collector Current

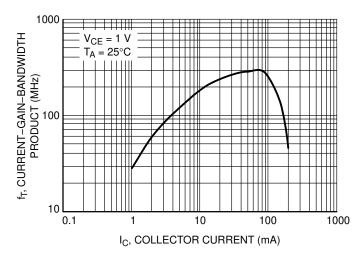


Figure 20. Current Gain Bandwidth Product vs. Collector Current

TYPICAL CHARACTERISTICS - BC807-40LT1

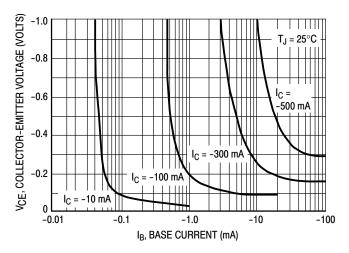


Figure 21. Saturation Region

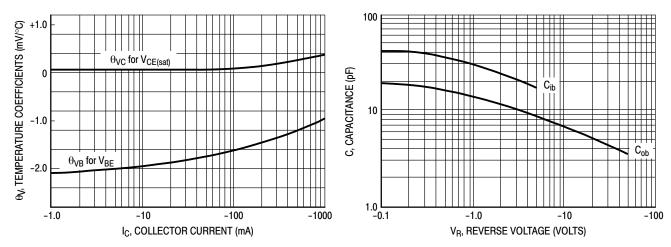


Figure 22. Temperature Coefficients

Figure 23. Capacitances

TYPICAL CHARACTERISTICS - BC807-16LT1, BC807-25LT1, BC807-40LT1

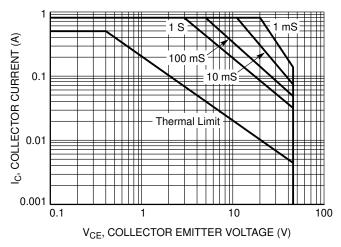
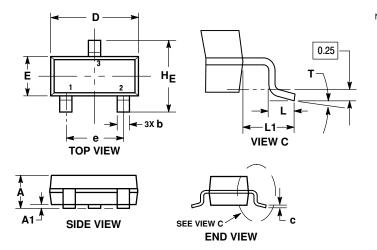


Figure 24. Safe Operating Area

PACKAGE DIMENSIONS

SOT-23 (TO-236) CASE 318-08 **ISSUE AR**



NOTES:

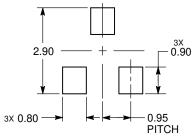
- DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994. CONTROLLING DIMENSION: MILLIMETERS. MAXIMUM LEAD THICKNESS IN THE MINIMUM THICKNESS OF MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF THE BASE MATERIAL.
 DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH,
- PROTRUSIONS, OR GATE BURRS

	MILLIMETERS			INCHES		
DIM	MIN	NOM	MAX	MIN	NOM	MAX
Α	0.89	1.00	1.11	0.035	0.039	0.044
A1	0.01	0.06	0.10	0.000	0.002	0.004
b	0.37	0.44	0.50	0.015	0.017	0.020
С	0.08	0.14	0.20	0.003	0.006	0.008
D	2.80	2.90	3.04	0.110	0.114	0.120
E	1.20	1.30	1.40	0.047	0.051	0.055
е	1.78	1.90	2.04	0.070	0.075	0.080
L	0.30	0.43	0.55	0.012	0.017	0.022
L1	0.35	0.54	0.69	0.014	0.021	0.027
HE	2.10	2.40	2.64	0.083	0.094	0.104
T	0°		10°	0°		10°

STYLE 6:

- PIN 1. BASE 2. EMITT
 - EMITTER
 - COLLECTOR

RECOMMENDED SOLDERING FOOTPRINT*



DIMENSIONS: MILLIMETERS

*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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